

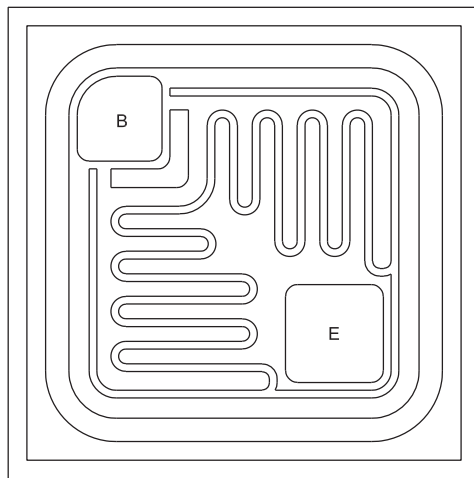
PROCESS CP303X
Small Signal Transistor
NPN - High Current Transistor Chip



PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	22 x 22 MILS
Die Thickness	5.9 MILS
Base Bonding Pad Area	3.7 x 3.7 MILS
Emitter Bonding Pad Area	4.2 x 4.2 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au-As - 13,000Å

GEOMETRY



BACKSIDE COLLECTOR R1

GROSS DIE PER 5 INCH WAFER

35,100

PRINCIPAL DEVICE TYPES

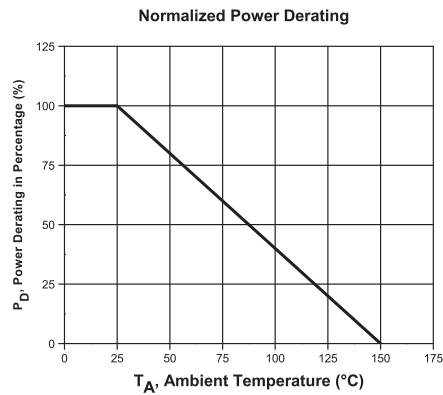
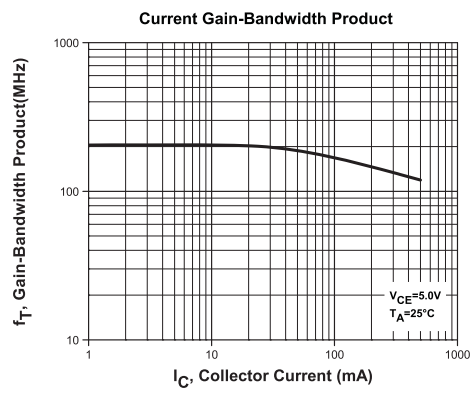
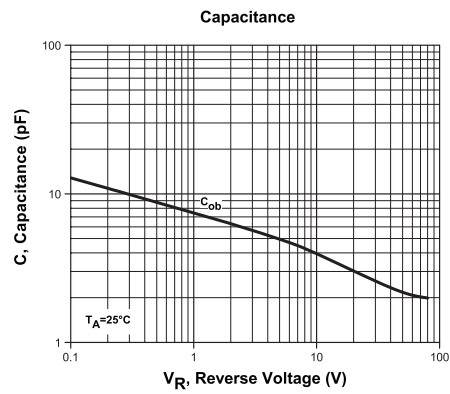
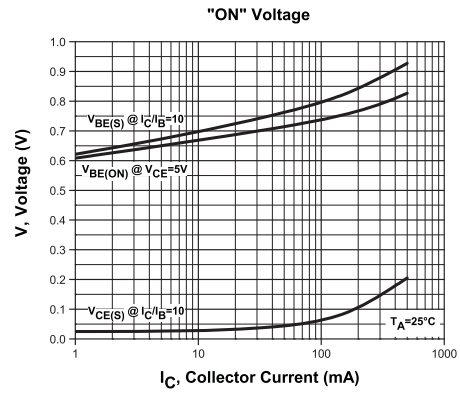
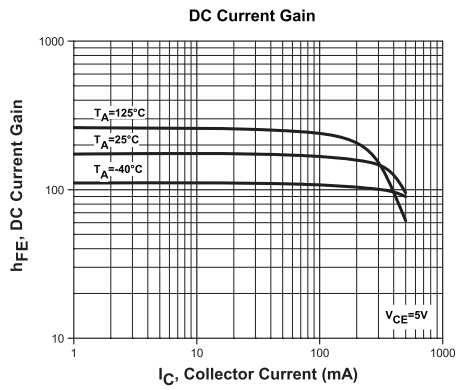
MPS8099

MPSA06

R0 (30-August 2011)

PROCESS CP303X

Typical Electrical Characteristics



R0 (30-August 2011)